



SHEET 1 OF 1

| <b>INFORMATION DISCLOSURE<br/>CITATION IN AN<br/>APPLICATION</b><br><br><b>(PTO-1449)</b> |          |  |                                | ATTY. DOCKET NO.<br><b>060188-0670</b>             | SERIAL NO.<br><b>10/676,877</b>   |             |
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|   |          |  |                                | APPLICANT<br><b>Taiji NODA</b>                     |   |             |
|   |          |  |                                | FILING DATE<br><b>October 02, 2003</b>             | GROUP<br><b>2822</b>  |             |
| <b>U.S. PATENT DOCUMENTS</b>  |          |  |                                |  |   |             |
| EXAMINER'S INITIALS   | CITE NO. | Document Number<br>Number-Kind Code <sub>2</sub> ( <i>if known</i> )   | Publication Date<br>MM-DD-YYYY | Name of Patentee or Applicant of Cited Document    | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |             |
| MT  |          | US 6,432,802 B   | 08/13/2002                     | NODA et al.  |   |             |
| MT  |          | US 6,184,112 B   | 02/06/2001                     | MASZARA et al.                                     |   |             |
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| <b>FOREIGN PATENT DOCUMENTS</b>   |          |  |                                |  |   |             |
| EXAMINER'S INITIALS   | CITE NO. | Foreign Patent Document<br>Country Codes-Number & Kind<br>Codes ( <i>if known</i> )  | Publication Date<br>MM-DD-YYYY | Name of Patentee or<br>Applicant of Cited Document | Pages, Columns, Lines<br>Where Relevant<br>Figures Appear                 | Translation |
|   |          |  |                                |  |   | Yes      No |
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| <b>OTHER ART</b> (Including Author, Title, Date, Pertinent Pages, Etc.)                   |          |  |                                |  |   |             |
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| MT  |          | JOHN, S et al.: "Strained Si n-channel metal-oxide-semiconductor transistor on relaxed Si <sub>1-x</sub> Gex formed by ion implantation of Ge," <i>Applied Physics Letters</i> , American Institute of Physics, April 5, 1999, Vo. 74, No. 14, pp. 2076-2078             |                                |  |   |             |
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| <b>EXAMINER</b><br><b>/Michael Trinh/</b>   |          |  |                                | <b>DATE CONSIDERED</b><br><b>06/28/2006</b>        |   |             |

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1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.